

# 全世界功率半導體資料手冊

**DATA**

**DATA**

**DATA**



全華科技圖書公司印行

# 編輯大意與程序

- 目的** 本書編輯目的在於廣泛報導全世界功率半導體界目前製造之情形。此類之書或將無法包羅讀者所需之全部資料，但本書確可提供讀者於設計之際選用適當型式及其製造廠商。
- 技術資料之獲取** 本書資料皆係由參與製造廠商通力合作，提供最新技術資料，再由本刊分類編輯而成。製造廠商提供該等資料均未索取任何報酬。
- JEDEC型號** 標準 1N, 2N, 3N 型號中所列電氣、機械及環境等特性，皆直接由 JEDEC 註冊登記發表而來。此等註冊製造廠商藉型號對照表中製造廠商代號後之符號加以表示。一般而言，JEDEC 也標有不同廠商製造之型號，不論是否已登記，只要規格相符即可，唯仍有少數例外，讀者不妨逕與製造廠商洽詢。
- 軍用型號** 在技術欄內，軍用型號所列電氣、機械及環境等特性均直接自合格軍用規格與標準中求得。每一型號之合格製造廠商則係來自 QPL (合格零件表) 或 QTL (合格檢驗函)。
- 代用型號與共同性** 本書雖非專為提供互換表而作，但由於編列安排，技術欄內所選列特性中，性質相同或相近者均集中一起。此種編排方式，使代用或互換零件更臻完善便捷及安全。
- 價格與可用性** 鑑於電子工業具有複雜且變化快速之特性，最新價格及交貨資料皆需與製造廠商洽詢。本書後頁所列製造廠商及當地辦公室一欄，將可提供此項協助。
- 製造廠商之規格** 本書包括最新製作之組件，組件之主要特性、圖形及製造廠商。所載內容，盡力確保其正確，唯錯誤與疏漏之處，仍所難免。最新之價格與完整之技術細節，需由製造廠商或其代理店方能提供。

# 如何使本書發揮最大效用

為使本書發揮最大效用，請在下面方框中選擇與您自身的已知—未知狀況相同的問題，再依文中的指示加以解決。

1.	<p>已知：電機與機械方面的要求 未知：適合的型號 指示：</p> <ol style="list-style-type: none"> <li>翻至首頁目錄表，選擇與元件型式有關的技術數據欄。</li> <li>翻到所選欄內的任一頁，注意每頁上角所示的編列參數（亦即數據中所列各特性）。</li> <li>應用編列參數，定出合於所求的一般性型號（由於編列安排的關係，此等型式將成群的出現）再由此中選取最合適者。</li> <li>如欲查明所選型號的製造廠商，請遵循下面(2)號方框的指示。</li> </ol>
2.	<p>已知：型號 (TIP 41, C 126 M) 未知：製造廠商，地址與辦公室 指示：</p> <ol style="list-style-type: none"> <li>翻至型號對照表（第一欄）定出型號。（請參照“型號對照表中，型號編列方法”）</li> <li>注意代表製造廠商的三或四個英文字母代號（Codes）。如 TII, GESY, 即表不同型式的製造廠商代號。</li> <li>應用書後的“製造廠商與其代號”（Manufacturers &amp; Their Codes），查出此代號的廠商。 （注意：製造商在美國辦公室，均以黑體字印在表中，再由書後一特別欄中，即可以查明）。</li> </ol>
3.	<p>已知：型號 (40DNH 120) 未知：電氣特性及／或外觀圖 指示：</p> <ol style="list-style-type: none"> <li>翻至“型號對照表”，定出其型號。</li> <li>注意頁數與行數，如 157-56。</li> <li>在技術欄內定出型號。 （注意：每一型號中與電氣及性能特性相並列的，為外觀參改考，其形狀可由 27 欄中查出）</li> </ol>
4.	<p>已知：型號 未知：可供取代的等效型號 指示：</p> <ol style="list-style-type: none"> <li>遵循(3)號方框的指示。</li> <li>觀察已知型號四周各型號，以決定最適當者加以取代或互換。</li> </ol>
5.	<p>已知：軍用要求 未知：適合的型號 指示：</p> <ol style="list-style-type: none"> <li>遵循(1)號方框的指示，決定適合軍用要求的一般型號，再由標明有 (JAN) 字首中選用軍用型式。</li> <li>如欲查明製造廠商，則請依照號方框(6)的指示。</li> </ol>
6.	<p>已知：軍用型號 未知：合格製造廠商，及合用的軍用規格。 指示：</p> <ol style="list-style-type: none"> <li>翻至 26 欄（美國軍用規格型式），定出型號（型號係依字母——數字順序排列）</li> <li>注意製造廠商代號，及列在型號後的詳細規格。（較一般性規格詳盡的詳細規格，係表列在詳細規格一行內，使元件的軍用規格得以完全。）</li> <li>請利用書後的“製造廠商及其代號”（Manufacturers &amp; Their Codes）查出製造廠商代號。</li> </ol>



## 技術欄內十的倍數，符號與編碼之應用

為能在最小的空間內，展示大量的資料，本書中的數據應用了下列的修改工具：

以下所示的十乘幕倍數係用在數字行中，當所測數值比行首所示的單位大甚多或小甚多時，即應用之，通常此等單位稱為基本單位。如V（電壓），A（安培），S（秒）等。此等倍數及其解釋如下：

倍 數				解 釋		
表示十的乘幕 (powers) 的字首 (prefixes) 與符號 (symbols) (由國際度量衡委員會提供，經美國國家標準局認可)				數據的數值	行首基本單位	實際表示數值
乘幕	字首	符號	乘幕	字首	符號	
$10^{12}$	tetra	T	$10^{-9}$	deka	da	$10^{-9}$ nano n
$10^9$	giga	G	$10^{-1}$	deci	d	$10^{-12}$ pico p
$10^6$	mega	M	$10^{-2}$	centi	c	$10^{-15}$ femto f
$10^3$	kilo	k	$10^{-3}$	milli	m	$10^{-18}$ atto a
$10^2$	hecto	h	$10^{-6}$	micro	$\mu$	10
				* 也可以寫成爲0.5而不加任何倍數		

### 符號與編碼

**符號：**在每一行中數字或其他地方，當數據數值與行首所示有所不同時，即當應用如#，△與S等符號，例如，當某一行首標明爲最大電功率（瓦）（Max. Power）時，若某一型式的數據爲最小電功率值則此中變化即需以一特別符號加在數值前面以作標識之用。

**注意：**本書所用的符號與編碼均在書後卡片中加以說明。

**編碼：**在某些行中，應用編碼以將數據加以簡化，此等編碼可以是字母（A. B. C等）數字（1. 2. 3等）或二者的組合

### 在型號對照表 (Type No. Cross-Index) 中型號編列方法

型號對照表中的型號編列依下列規則而排：

	例
規則：1) 型號係按數字—字母順序而排列，即以數字開始（小數，分數或整數）的型號排在以英文字母開頭的型號前面。	13A01 143 1202 A147 AN127 B20000
2) 小數及分數在整個數字前。若剩下的型號相同，則以小數開頭的型號排列分數開頭的型號前面。	25Z150 $\frac{1}{4}$ Z150 $\frac{3}{4}$ M12Z 1T3
3) 一般編列時，零皆予忽略，但若零爲唯一區分二種型號的基數時例外，此種情況下含零的型號需將置於首位。	0112 112 0113 00115 AP01 AP1 AP02
4) 集中在連號（-）或斜劃（/）前的字母，爲編列時的控制因數（Controlling Factors）。以相同數字/字母開頭而在其後爲連號或斜劃的型號是排在相同位置爲字母的型號前面。	66-0706 66M1 70/10 70A9
5) 軍用字首（JAN）在型號數字—字母編列時均予忽略，軍用型號直接遵循JEDEC等效型號。	2N645 JAN2N645

# 如何使本書發揮最大效用

在技術欄中，型號的安排主要係由每欄內所列的一般特性中，選擇出特別重要者。這些選出的特性即為編列參數，在每一欄中編列參數均不同，可由每一頁上角加以查明。下例即可協助讀者明瞭。

主要特性										編列參數						
LINE No.	TYPE No.	AVE FWD CURR	RECT. CURR	3 MAX REPEAT SURGE CURR @ 25°C	MAX RATING SURGE CURR	POWER DISS	MAX. OPER TEMP	MAXIMUM FORWARD VOLTAGE DROP		MAX. REVERSE CURR. IR		AVALANCHE RATINGS		MAT.	PACKAGE (DWG) (No.)	
		1 IF(AV) (A)	2 @TEMP (C)	PK.RV (V)	4 IFSM (A)	PULSE WIDTH (s)	(C)	VF (V)	@ IF (A)	@ TEMP (C)	@ 25°C & VR (A)	@ T & VR (A)	TEST T (C)			TEST VR (V)
5					.2 整流器：低電流											

順序為 (1)IF(AV) (2)TEMP (3)VRRM (4)IFSM AND (5)TYPE No.

每一欄內不同型式，係由第一個編列參數，依數字或字母的順序加以排列。若有一群第一參數相同的型式，即由其第二個參數的順序來安排。此種情況一直延續到最後一個參數為止，在每一例中，此數字即為型號本身。型號安排的最後一步是採取和型號對照表中相同的方法以與型號順序相符，如前文中所述。

下圖所示為一經簡化後的排列模式。

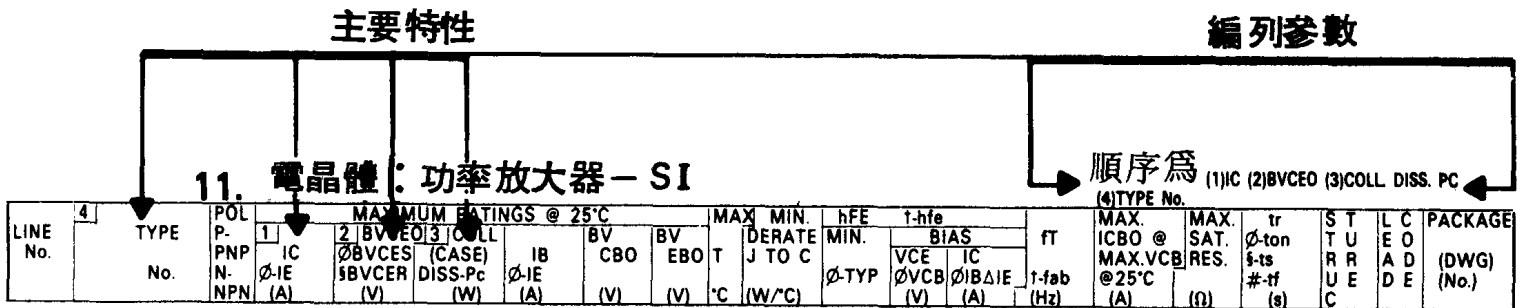
4 型號	特性			
	1 A	2 B	C	3 D
A13	100		325	
A4	100		1000	20
A9	100	A	20	25
A10	100	A	200	25
A3	100	B	40	15
A1	100	C	80	10
A8	100	C	900	15
A7	100	D	35	30
A11	110	A	60	25
A2	120	A	300	15
A5	120	B	150	20
A6	120	B	200	20
A12	120	B	475	25

最後編列參數
第一編列參數
第二編列參數
並未編列
第三編列參數

注意在任一編列參數中若缺少一項均視為零，并編列在有實際數值的項之前。

# HOW TYPE NOS. ARE ARRANGED IN THE TECHNICAL SECTION – SEQUENCING PARAMETERS

在技術欄中，型號的安排主要係由每欄內所列的一般性中，選擇出特別重要者。這些選出的特性即為編列參數，在每一欄中編列參數均不同，可由每一頁上角加以查明。下例即可協助讀者明瞭。



每一欄內不同型式，係由第一個編列參數，依數字或字母的順序加以排列。若有一群第一參數相同的型式，即由其第二個參數的順序來安排。此種情況一直延續到最後一個參數為止，在每一例中，此數字即為型號本身。型號安排的最後一步是採取和型號對照表中相同的方法以與型號順序相符，如前文中所述。下圖所示為一經簡化後的排列模式。

4	型號	特性			
		1 A	2 B	C	3 D
	A13	100		325	
	A4	100		1000	20
	A9	100	A	20	25
	A1C	100	A	200	25
	A3	100	B	40	15
	A1	100	C	80	10
	A8	100	C	900	15
	A7	100	D	35	30
	A1	110	A	60	25
	A2	120	A	300	15
	A5	120	B	150	20
	A6	120	B	200	20
	A12	120	B	475	25

最後編列參數
第一編列參數
第二編列參數
並未編列
第三編列參數

注意在任一編列參數中若缺少一項均視為零，并編列在有實際數值的項之前。

# DEFINITIONS AND INTERPRETATIONS

**POWER SEMICONDUCTORS** as interpreted by D.A.T.A., consist of Diodes, Transistors and Thyristors which fall within the stated ranges of current and wattage. The ranges used represent a consensus from users, manufacturers and technical information agencies, presented by D.A.T.A. for the purpose of highlighting the increasing use of semiconductor devices in high-current, high-power applications. This then is D.A.T.A.'s interpretation of Power Semiconductors. D.A.T.A. expects and welcomes comments and suggestions designed to improve this power presentation for the user and for the participating manufacturers. Every effort will be made to incorporate suggestions in future editions.

Device types listed in the **POWER SEMICONDUCTOR D.A.T.A.BOOK<sup>®</sup>** are defined below:

**RECTIFIER:** A two-terminal device with a reverse-blocking voltage current characteristic.

**FAST-RECOVERY RECTIFIER:** A two-terminal, reverse-blocking device, with a relatively short recovery time when suddenly biased from a forward (conducting) to a reverse (blocking) state.

**ZENER DIODE:** A two-terminal voltage regulator with an essentially constant terminal voltage over its operating current range in the breakdown region.

**AMPLIFIER TRANSISTOR:** A three-terminal, two-junction NPN or PNP device used to provide power amplification.

**SWITCHING TRANSISTOR:** An amplifier transistor with relatively high frequency power control rate when switched between its voltage-saturation region and its current-cutoff region.

**SILICON CONTROLLED RECTIFIER (SCR):** A three-terminal, four-layer reverse-blocking thyristor, gated with a positive voltage (P-gate).

**FAST-SWITCHING SCR:** A three-terminal, four-layer reverse-blocking SCR with relatively fast turn-off time (commutation speed).

**TRIAC:** A three-terminal, multi-layer, bidirectional thyristor with four-quadrant gate turn-on capability (gate voltage positive or negative relative to main terminal 1).

**MISCELLANEOUS POWER THYRISTORS:**

**N-GATE THYRISTOR:** A three-terminal, multi-layer, reverse-blocking thyristor, gated with a negative voltage. Distributed amplified gates are included in the category because of their negative gate voltage requirements.

**REVERSE CONDUCTING THYRISTOR:** A three-terminal, multi-layer, reverse-conducting thyristor, gated with a positive voltage and conducting large currents in the reverse direction.

# DEFINITIONS AND INTERPRETATIONS (Cont'd)

Device types listed in the POWER SEMICONDUCTOR D.A.T.A.BOOK with ranges of primary characteristics and ratings are shown below:

DEVICE TYPE	RANGES OF CHARACTERISTICS & RATINGS INCLUDED		
Rectifiers	Low Current	10 to 49 Amps	$I_F$ (AV)
	Medium Current	50 to 199 Amps	$I_F$ (AV)
	High Current	$\geq 200$ Amps	$I_F$ (AV)
Fast Recovery Rectifiers	$\geq 10$ Amps		$I_F$ (AV)
	$t_{rr}$ range		10 nsec to 10 $\mu$ sec
Power Zeners	$\geq 10$ Watts		Max. Dissipation
Transistors	Power Amplifiers-Germanium		$\geq 1$ Amp $I_c$ , 50 Watts $P_c$ , 450 mw/ $^{\circ}$ C
	Power Amplifiers-Silicon		$\geq 1$ Amp $I_c$ , 50 Watts $P_c$ , 450 mw/ $^{\circ}$ C
	Power Switching		$\geq 1$ Amp $I_c$ , 50 Watts $P_c$ , 450 mw/ $^{\circ}$ C
	Power Darlington		$\geq 1$ Amp $I_c$ , 50 Watts $P_c$ , 450 mw/ $^{\circ}$ C $f_T$ up to 400 MHz
SCRs	Low Current	10 to 49 Amps	$I_T$ (RMS)
	Medium Current	50 to 199 Amps	$I_T$ (RMS)
	High Current	$\geq 200$ Amps	$I_T$ (RMS)
Fast-Switching SCRs	$\geq 10$ Amps		$I_T$ (RMS)
	$t_q$ in the range of		50 $\mu$ sec max.
Triacs	$\geq 10$ Amps		$I_T$ (RMS)
Miscellaneous Power Thyristors	$\geq 10$ Amps		$I_T$ (RMS)



# EXPLANATIONS OF CHARACTERISTICS AND RATINGS

**RECTIFIERS, ZENERS:** The characteristics and ratings shown are generally for the worst-case condition. This approach allows the reader to compare and select devices whose characteristics are stated to be under maximum operating conditions. In general, characteristics and ratings are measured at a temperature of 25°C.

- A/V — Slope of Volt-Amp characteristic of avalanche rectifiers at breakdown (A/V)
- C<sub>j</sub> — Diode junction capacitance (Farad)
- di/dt — Rate of reversal of device current (Amp/μSec)
- I<sub>F</sub> — Forward DC current (Amp)
- I<sub>F</sub> (AV) — Average forward DC current (Amp)
- I<sub>FSM</sub> — Maximum forward surge current (Amp)
- I<sub>R</sub> — Reverse current (Amp)
- I<sub>RM</sub> (REC) — Maximum (Peak) reverse recovery current (Amp)
- I<sub>rr</sub> — Reverse recovery current to which trr is measured (Amp)
- I<sub>Z</sub> — Reference diode current at breakdown (Amp)
- I<sub>ZT</sub> — Test current at which reference voltage is measured for reference diodes (Amp)
- P<sub>F</sub> — Forward power dissipation (Watt)
- P<sub>R</sub> — Reverse power dissipation (Watt)
- Q<sub>s</sub> — Stored charge during recovery (Coul)  $Q_s = \int_0^{trr} i_r dt$
- R<sub>L</sub> — Circuit load resistance (Ohm)
- T — Device operating temperature for test mode (°C)
- T<sub>C</sub> — Temperature coefficient of voltage for reference diode (Volt/°C)
- t<sub>p</sub> — Pulse width (duration) of applied current or voltage (Sec)
- t<sub>fr</sub> — Forward recovery time (Sec)
- trr — Reverse recovery time (Sec)
- T<sub>max</sub> — Maximum operating temperature of device (°C)
- V<sub>F</sub> — Forward DC voltage (Volt)
- V<sub>R</sub>(TEST) — Reverse voltage at which I<sub>R</sub> is measured (Volt)
- V<sub>RRM</sub> — Maximum reverse repetitive voltage (Volt)
- V<sub>Z</sub> — Voltage across a reference diode at breakdown (Volt)
- Z<sub>R</sub> — Reverse circuit impedance during recovery period (Ohm)
- Z<sub>Z</sub> — Small signal dynamic impedance of a reference diode at breakdown (Ohm)

# EXPLANATIONS OF CHARACTERISTICS AND RATINGS (Cont'd)

**TRANSISTORS:** The characteristics and ratings shown are generally for the worst-case condition. This approach allows the reader to compare and select devices whose characteristics are stated to be under maximum operating conditions. In general, characteristics and ratings are measured at a temperature of 25°C.

$BV_{CBO}$	– Breakdown voltage, collector-to-base; emitter open-circuit. (Volt)	$I_C$	– Collector current, DC. (Amp)
$V_{(BR)CBO}$		$I_{C(Sat)}$	– Collector saturation current. (Amp)
$BV_{CEO}$	– Breakdown voltage, collector-to-emitter; base open-circuit. (Volt)	$I_{CBO}$	– Collector cut-off current, DC, emitter open-circuit. (Amp)
$V_{(BR)CEO}$		$I_{CES}$	– Collector cut-off current, DC, with base shorted to emitter. (Amp)
$BV_{CER}$	– Breakdown voltage, collector-to-emitter; with specified base-to-emitter resistance. (Volt)	$I_{CEX}$	– Collector cut-off current, DC, with specified circuit between base and emitter. (Amp)
$V_{(BR)CER}$		$I_{P(3)}$	– Third order intercept point.
$BV_{CES}$	– Breakdown voltage, collector-to-emitter; with base short-circuit to emitter. (Volt)	NF	– Noise factor or noise figure. (db)
$V_{(BR)CES}$		$\lambda_s$	– Wave length of maximum sensitivity. (Meter)
$BV_{CEX}$	– Breakdown voltage, collector-to-emitter; with specified circuit between base and emitter. (Volt)	$P_c$	– Collector power dissipation. (Watt)
$V_{(BR)CEX}$		$P_d$	– Power dissipation. (Watt)
$BV_{EBO}$	– Breakdown voltage, emitter-to-base; collector open-circuit. (Volt)	$P_o$	– Power output. (Watt)
$V_{(BR)EBO}$		$P_{o1db}$	– Power output at 1.0 db compression point. (Watt)
$C_{ob}$	– Output capacitance with input AC open-circuit, common base. (Farad)	$P_T$	– Total power dissipation (Watt)
$f_{ab}$	– Small-signal short-circuit forward current transfer ratio cut-off frequency, common base (alpha cut-off frequency). (Hz)	$R_{BBO}$	– Interbase resistance, with emitter open circuit. (Ohm)
$f_{hfb}$		$t_d$	– Delay time. (Sec.)
$f_{ae}$	– Small-signal short-circuit forward current transfer ratio cut-off frequency, common emitter (beta cut-off frequency). (Hz)	$t_f$	– Fall time. (Sec.)
$f_{hfe}$		$t_{off}$	– Turn-off time = $t_s + t_f$ . (Sec.)
$f_T$	– Extrapolated unity gain frequency (gain bandwidth product). Product of the common-emitter current transfer ratio and the frequency of measurement at a frequency where the current gain is decreasing at the rate of 6 db per octave. This frequency is also known as the Transition Frequency. (Hz)	$t_{on}$	– Turn-on time = $t_d + t_r$ . (Sec.)
$h_{FE}$	– DC forward current transfer ratio, common emitter.	$t_r$	– Rise time. (Sec.)
$h_{fo}$	– Small signal forward current transfer ratio, common emitter.	$t_s$	– Storage time. (Sec.)
$h_{ib}$	– Small signal value of the short-circuit input impedance, common base. (Ohm)	$V_{BE}$	– Base-to-emitter voltage, DC. (Volt)
$h_{ie}$	– Small signal value of the short-circuit input impedance, common emitter. (Ohm)	$V_{BE(Sat)}$	– Base-to-emitter saturation voltage. (Volt)
$h_{ob}$	– Small signal value of the open-circuit output admittance, common base. (mho)	$V_{CB}$	– Collector-to-base voltage, DC. (Volt)
$h_{oe}$	– Small signal value of the open-circuit output admittance, common emitter. (mho)	$V_{CBO}$	– Collector-to-base voltage, DC, emitter open. (Volt)
$h_{rb}$	– Small signal value of the open-circuit reverse voltage transfer ratio, common base.	$V_{CC}$	– Supply voltage. (Volt)
$h_{re}$	– Small signal value of the open-circuit reverse voltage transfer ratio, common emitter.	$V_{CE}$	– Collector-to-emitter voltage, DC. (Volt)
$I_B$	– Base current, DC. (Amp)	$V_{CE(Sat)}$	– Collector-to-emitter saturation voltage. (Volt)
$I_{B(Sat)}$	– Base saturation current. (Amp)	$V_{CEO}$	– Collector-to-emitter voltage, DC, base open. (Volt)
		$V_{EBO}$	– Emitter-to-base voltage, DC, collector open. (Volt)
		$V_{off}$	– Offset voltage. (Volt)
		$Y_{FE}$	– DC forward transmittance with output short-circuit. (mho)

# EXPLANATIONS OF CHARACTERISTICS AND RATINGS (Cont'd)

**SCR, TRIACS & MISCELLANEOUS POWER THYRISTORS:** The characteristics and ratings shown are generally for the worst-case condition. This approach allows the reader to compare and select devices whose characteristics are stated to be under maximum operating conditions. In general, characteristics and ratings are measured at a temperature of 25°C. The only exception is  $V_{DRM}$  (maximum repetitive off-state voltage) which is given over the operating temperature range.

$di/dt$  (RATING): critical rate of rise of on-state current (Amp/ $\mu$ sec)

$dv/dt$  (COMMUTATING): critical rate of rise of commutating voltage (Volt/sec)

$dv/dt$  (STATIC): critical rate of rise of off-state voltage (Volt/sec)

$I_{CT}$ : N-gate trigger current (Amp)

$I_D @ T_{ref} @ V_{DRM}$ : Off-state-current (Amp)

$I_{GO}$ : Gate Turn-off current (Amp)

$I_{GT}$ : Gate trigger current (Amp)

$I_H$ : Holding current (Amp)

$I_L$ : Latching current (Amp)

$I_R$ : Reverse current (Amp)

$I_S @ V_S$ : Switching current (Amp)

$I_T @ T_{ref}$ : Static on-state current (Amp)

$I_{T(AV)} @ T_{ref}$ : The average sinewave on-state current (Amp)

$I_{TRM}$ : Maximum repetitive on-state current (Amp)

$I_{T(RMS)} @ T_{ref}$ : RMS on-state current (Amp)

$I_{TSM}$ : Surge current (Amp)

$t_{gt}$ : Gate-controlled turn-on time (Sec)

$t_{on}$ : Switching turn-on time (Sec)

$t_q$ : Circuit-Commutated turn-off time (Sec)

$V_{CT}$ : N-gate trigger voltage (Volt)

$V_D$ : DC blocking volts (Volt)

$V_{DRM}$ : Repetitive peak off-state voltage (Volt)

$V_{GQ}$ : Gate turn-off voltage (Volt)

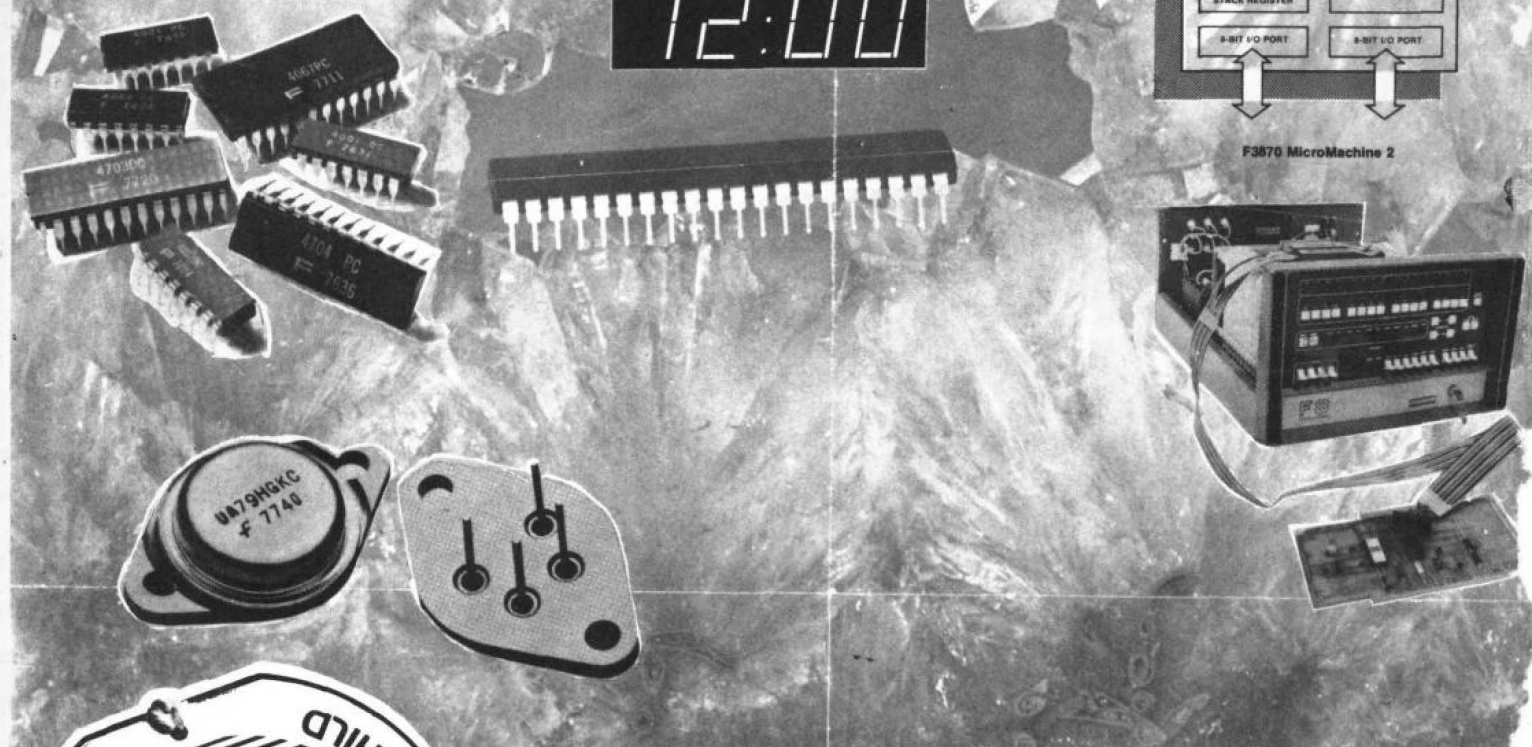
$V_{GT}$ : Gate trigger voltage (Volt)

$V_{RRM}$ : Max. reverse repetitive voltage (Volt)

$V_T @ I_T$ : On-state voltage (Volt)

**WE FEATURE SPEEDY DELIVERY OF FAIRCHILD'S SPEEDY CMOS.**

Fairchild's CMOS delivers higher speed and greater density at competitive prices. And we can deliver Fairchild CMOS. Fast. The secret that makes Fairchild's family of SSI, MSI and LSI CMOS ICs such great performers is their Isoplanar C processing.



**FAIRCHILD FROM**

**FAIRCHILD SEMICONDUCTOR (TAIWAN) LTD.**  
 台灣快捷半導體有限公司  
 台北市中山北路三段47號協志大樓502室  
 TEL: (02) 5973205~7

**\* OR FROM DISTRIBUTORS \***

**SOLID STATE**

**全智有限公司**  
 ULTRALITE CORPORATION  
 台北市長安東路2段73號之1三樓  
 TEL: (02)5214433 • 5214463  
 5615563  
 TELEX: 21395 CIETC  
 CABLE: CIETC TAIPEI

**昌貿企業有限公司**  
 TAITRON ENTERPRISE CO., LTD.  
 台北市長安西路78巷4弄9之2號2樓  
 TEL: (02)5612036 • 5111502  
 TWX: 22309 GINCOR  
 ATT TAITRON  
 CABLE: TAITRON TAIPEI

**殷實企業股份有限公司**  
 GOOD FAITH WORLDWIDE  
 INTERNATIONAL CO., LTD.  
 台北市南陽街13號5樓  
 TEL: (02)3612023  
 TELEX: 11862 GDFH  
 CABLE: GDFH TAIPEI

**MICROPROCESSOR**

**領先企業股份有限公司**  
 TECA ENGINEERING CO., LTD.  
 台北市仁愛路二段98號5樓  
 TEL: 3511775/76 / 79  
 TELEX: 11303 YSCYK  
 11498 GOLDEN GA  
 工廠: 台北市永吉路23號

**TECHNOLOGY INSTRUMENTATION**

**同康貿易股份有限公司**  
 UNIVERSAL TRADING CORPORATION  
 台北市中山北路3段49號  
 中山商業大樓 503室  
 TEL: (02)5919215~8

(按筆劃順序排序)



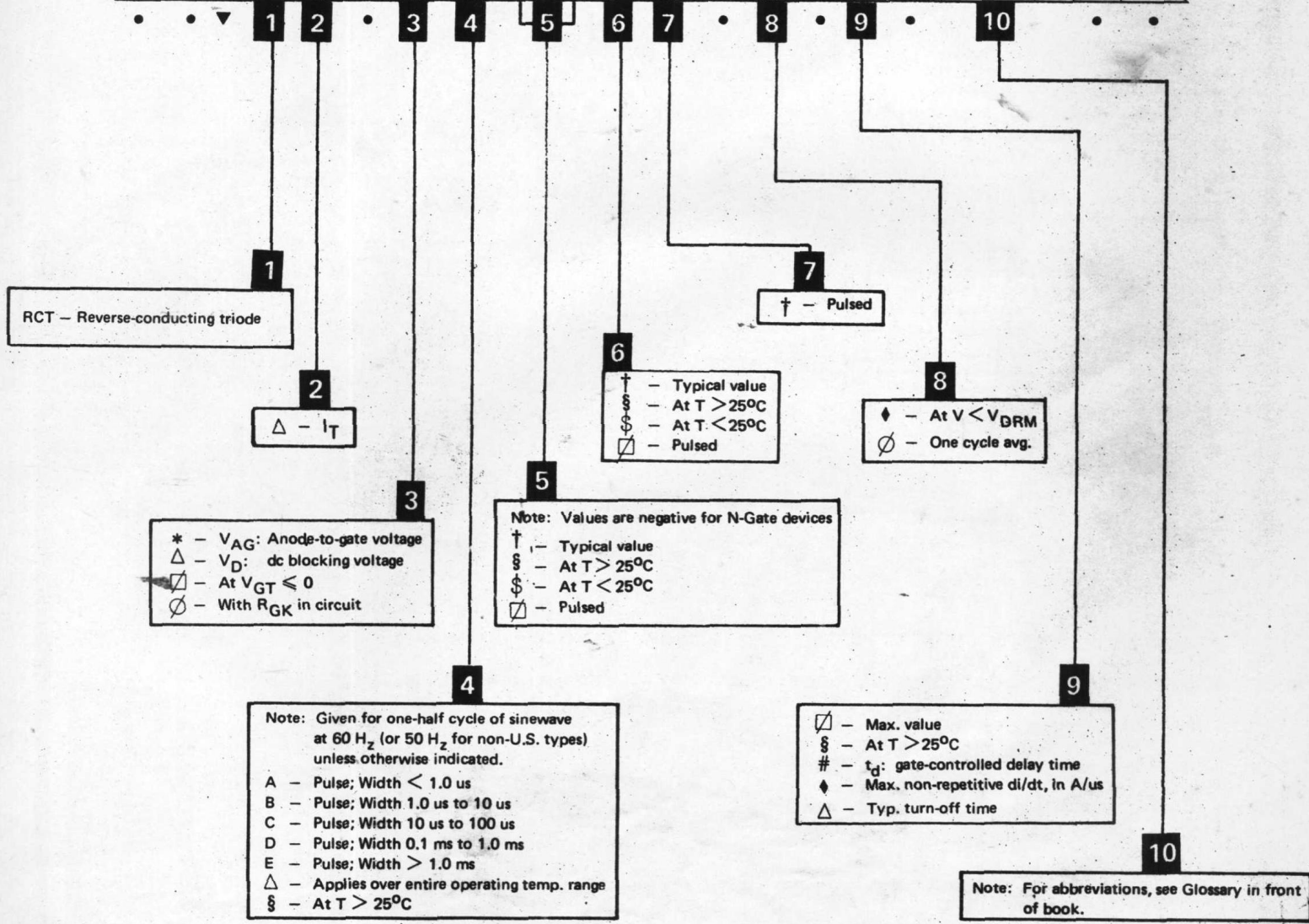
## THYRISTOR (Cont'd)

### SYMBOLS AND CODES EXPLAINED (INTERPRETER)

#### 25. MISCELLANEOUS POWER THYRISTORS

LINE No.	TYPE No.	1		2	3	4	5		6	7	8	9	10	LEAD CODE	PACKAGE (DWG) (No.)
		USE CODE	IT				MAX. RMS ON-ST. CURR. (RMS) (A)	TEMP (°C)							

IN ORDER OF (1)USE CODE (2)MAX. IT(RMS) (3)TEMP. (4)VDRM (5)ITSM AND (6)TYPE No.



• See Symbols and Codes Common To More than One Section at Top of Page PW-5

▼ See Type No. Symbols and Codes At Top of Page PW-5

# 全世界功率半導體資料手冊

## 目錄

### 應用指南

如何使本書發揮最大效用 .....	iii
測量單位是如何表示 .....	iv
型號在型號對照表 (TYPE NO. CROSS INDEX) 中的編列方法 .....	iv
型號在技術欄 (TECHNICAL SECTION) 中的編列方法 .....	v-vi
定義與解釋 .....	vii-viii
特性與額定值的說明 .....	ix-xi

### 型號對照表 (TYPE NO. CROSS INDEX)

1 所有型式 .....	2-114
--------------	-------

### 技術欄 (TECHNICAL SECTIONS)

2 整流器：低電流 (10~49安) .....	115-132
3 整流器：中電流 (50~199安) .....	133-145
4 整流器：高電流 (200安以上) .....	146-171
5 快速復原整流器 (10安以上) .....	172-186
6 功率型齊納二極體 (10瓦以上) .....	187-200
7-9 (保留)	
10 電晶體：功率放大器 (鍍製) (1安以上) .....	201-210
11 電晶體：功率放大器 (矽製) (1安以上) .....	211-272
12 電晶體：功率交換用 (1安以上) .....	273-294
注意：這些型號在 10, 11, 13 欄中也列出 (此欄中包括了一些交換資料)	
13 電晶體：功率型達靈頓 (1安以上) .....	295-300
14-19 (保留)	
20 SCR：低電流 (10~49安) .....	301-324
21 SCR：中電流 (50~199安) .....	325-352
22 SCR：高電流 (200安以上) .....	353-399
23 快速交換 SCR (10安以上) .....	400-435
24 Triacs (10安以上) .....	436-449
25 其他功率電晶體 (10安以上) .....	450
包括 N 型閘裝置 (NGT) 及反向導電三極體 (RCT)	

### 補充欄

26 具有美國軍用規格之型式 .....	451-455
27 外觀圖 .....	456-568
JEDEC 指定規格 .....	561
引線編碼的辨認 - 電晶體 .....	567
閘流體 .....	568
28 製造廠在美辦公室 .....	569-615
29 製造廠編碼、名稱及地址 .....	616-618
30 製造廠商標 .....	619-624
符號與編碼說明 .....	見書後

出版者 全華科技圖書公司  
北市建國北路85巷9號  
電話：581-1300  
郵撥：100836

發行者 蕭而鄺  
印刷者 永輝彩藝印製廠







# 1. TYPE No. CROSS INDEX

IN TYPE NUMBER SEQUENCE

TYPE No.	MFRS	Pg&Line	TYPE No.	MFRS	Pg&Line	TYPE No.	MFRS	Pg&Line	TYPE No.	MFRS	Pg&Line	TYPE No.	MFRS	Pg&Line															
1N1355 (cont.)	SCN ♦SIE SPE STM TRW		1N1380A (cont.)	GSE ♦INR INRB INRJ MOTA NAE SCE SES SOD SPE SSI		1N1384A (cont.)	SSI SOD STM TRW IDC IDC IDC INRB INRJ MOTA NAE SCE SES SOD SPE SSI		1N1389 (cont.)	ETC IDC INRB INRJ MOTA MULB SAR SCN ♦SIE SSI STM CSR ETC IDC ♦INR INRJ MOTA NAE SCE SES SOD SPE SSI		1N1373A (cont.)	ETC IDC INRB INRJ MOTA SAR SCN SES SOD ♦SIE SSI STM CSR ETC IDC ♦INR INRJ MOTA MULB SAR SCN SES SOD SPE SSI		ESP GSE ♦INR INRI INRJ MOTA NAE SCE SES SOD SPE SSI	191-176	194-207	195-63	196-160	198-11	198-77								
1N1356A	CSR ETC IDC ♦INR INRI INRJ MOTA MULB SAR SCN ♦SIE SSI STM CSR ETC IDC ♦INR INRJ MOTA MULB SAR SCN SES SOD SPE SSI	191-177	1N1380B	SSA SAR	193-104	1N1385	CSR ETC IDC ♦INR INRJ MOTA NAE SCE SES SOD SPE SSI	193-188	1N1365A	ESP GSE ♦INR INRI INRJ MOTA MULB SAR SCN SES SOD SPE SSI	195-64	1N1369B	IDC SAR	196-161	1N1356B	IDC IDC INRB INRJ MOTA MULB SAR SCN ♦SIE SSI	191-177	1N1365B	TRW IDC IDC INRB INRJ MOTA MULB SAR SCN SES SOD SPE SSI	195-65	1N1370A	ESP GSE ♦INR INRI INRJ MOTA MULB SAR SCN SES SOD SPE SSI	197-22	1N1373B	SAR	198-11	1N1374	CSR ETC IDC ♦INR INRJ MOTA SAR SCN SES SOD SPE SSI	198-77
1N1357	CSR ETC IDC ♦INR INRI INRJ MOTA MULB SAR SCN ♦SIE SSI	192-54	1N1381	CSR ETC IDC ♦INR INRJ MOTA MULB SAR SCN SES SOD SPE SSI	193-189	1N1365A	ESP GSE ♦INR INRI INRJ MOTA MULB SAR SCN SES SOD SPE SSI	195-64	1N1369B	IDC SAR	196-161	1N1357A	CSR ETC IDC ♦INR INRI INRJ MOTA MULB SAR SCN SES SOD SPE SSI	192-55	1N1365B	TRW IDC IDC INRB INRJ MOTA MULB SAR SCN SES SOD SPE SSI	195-134	1N1370A	ESP GSE ♦INR INRI INRJ MOTA MULB SAR SCN SES SOD SPE SSI	197-22	1N1374A	ESP GSE ♦INR INRI INRJ MOTA SAR SCN SES SOD SPE SSI	198-78						
1N1357A	ESP GSE ♦INR INRI INRJ MOTA MULB SAR SCN SES SOD SPE SSI	192-55	1N1381A	ESP GSE ♦INR INRJ MOTA MULB SAR SCN SES SOD SPE SSI	193-189	1N1366A	CSR ETC IDC ♦INR INRJ MOTA MULB SAR SCN SES SOD SPE SSI	195-65	1N1370B	SAR	197-23	1N1357B	IDC IDC INRB INRJ MOTA MULB SAR SCN SES SOD SPE SSI	192-56	1N1366B	TRW IDC IDC INRB INRJ MOTA MULB SAR SCN SES SOD SPE SSI	195-135	1N1371A	ESP GSE ♦INR INRI INRJ MOTA MULB SAR SCN SES SOD SPE SSI	197-81	1N1375	CSR ETC IDC ♦INR INRJ MOTA MULB SAR SCN SES SOD SPE SSI	198-135						
1N1357B	IDC IDC INRB INRJ MOTA MULB SAR SCN SES SOD SPE SSI	192-56	1N1381B	IDC IDC INRB INRJ MOTA MULB SAR SCN SES SOD SPE SSI	193-190	1N1366A	CSR ETC IDC ♦INR INRJ MOTA MULB SAR SCN SES SOD SPE SSI	195-135	1N1371B	SAR	197-82	1N1358	CSR ETC IDC ♦INR INRI INRJ MOTA MULB SAR SCN SES SOD SPE SSI	192-154	1N1366B	TRW IDC IDC INRB INRJ MOTA MULB SAR SCN SES SOD SPE SSI	195-136	1N1371	CSR ETC IDC ♦INR INRJ MOTA MULB SAR SCN SES SOD SPE SSI	197-81	1N1375A	ESP GSE ♦INR INRI INRJ MOTA MULB SAR SCN SES SOD SPE SSI	198-136						
1N1358	CSR ETC IDC ♦INR INRI INRJ MOTA MULB SAR SCN SES SOD SPE SSI	192-154	1N1382	CSR ETC IDC ♦INR INRJ MOTA MULB SAR SCN SES SOD SPE SSI	194-61	1N1366A	CSR ETC IDC ♦INR INRJ MOTA MULB SAR SCN SES SOD SPE SSI	195-135	1N1371A	ESP GSE ♦INR INRI INRJ MOTA MULB SAR SCN SES SOD SPE SSI	197-81	1N1375A	ESP GSE ♦INR INRI INRJ MOTA MULB SAR SCN SES SOD SPE SSI	198-136	1N1366B	TRW IDC IDC INRB INRJ MOTA MULB SAR SCN SES SOD SPE SSI	195-136	1N1371	CSR ETC IDC ♦INR INRJ MOTA MULB SAR SCN SES SOD SPE SSI	197-81	1N1375A	ESP GSE ♦INR INRI INRJ MOTA MULB SAR SCN SES SOD SPE SSI	198-136						
1N1358A	ESP GSE ♦INR INRI INRJ MOTA MULB SAR SCN SES SOD SPE SSI	192-155	1N1382A	ESP GSE ♦INR INRJ MOTA MULB SAR SCN SES SOD SPE SSI	194-62	1N1366A	CSR ETC IDC ♦INR INRJ MOTA MULB SAR SCN SES SOD SPE SSI	195-135	1N1371B	SAR	197-82	1N1358A	ESP GSE ♦INR INRI INRJ MOTA MULB SAR SCN SES SOD SPE SSI	192-155	1N1366B	TRW IDC IDC INRB INRJ MOTA MULB SAR SCN SES SOD SPE SSI	195-136	1N1371	CSR ETC IDC ♦INR INRJ MOTA MULB SAR SCN SES SOD SPE SSI	197-81	1N1375A	ESP GSE ♦INR INRI INRJ MOTA MULB SAR SCN SES SOD SPE SSI	198-136						
1N1358B	SSA SAR	192-156	1N1382B	IDC IDC INRB INRJ MOTA MULB SAR SCN SES SOD SPE SSI	194-63	1N1366A	CSR ETC IDC ♦INR INRJ MOTA MULB SAR SCN SES SOD SPE SSI	195-135	1N1371A	ESP GSE ♦INR INRI INRJ MOTA MULB SAR SCN SES SOD SPE SSI	197-82	1N1358B	SSA SAR	192-156	1N1366B	TRW IDC IDC INRB INRJ MOTA MULB SAR SCN SES SOD SPE SSI	195-136	1N1371	CSR ETC IDC ♦INR INRJ MOTA MULB SAR SCN SES SOD SPE SSI	197-81	1N1375A	ESP GSE ♦INR INRI INRJ MOTA MULB SAR SCN SES SOD SPE SSI	198-136						
1N1359	CSR ETC IDC ♦INR INRI INRJ MOTA MULB SAR SCN SES SOD SPE SSI	193-17	1N1383	CSR ETC IDC ♦INR INRJ MOTA MULB SAR SCN SES SOD SPE SSI	194-130	1N1366A	CSR ETC IDC ♦INR INRJ MOTA MULB SAR SCN SES SOD SPE SSI	195-135	1N1371B	SAR	197-83	1N1359	CSR ETC IDC ♦INR INRI INRJ MOTA MULB SAR SCN SES SOD SPE SSI	193-17	1N1366B	TRW IDC IDC INRB INRJ MOTA MULB SAR SCN SES SOD SPE SSI	195-136	1N1371	CSR ETC IDC ♦INR INRJ MOTA MULB SAR SCN SES SOD SPE SSI	197-81	1N1375A	ESP GSE ♦INR INRI INRJ MOTA MULB SAR SCN SES SOD SPE SSI	198-136						
1N1359A	ESP GSE ♦INR INRI INRJ MOTA MULB SAR SCN SES SOD SPE SSI	193-18	1N1383A	ESP GSE ♦INR INRJ MOTA MULB SAR SCN SES SOD SPE SSI	194-131	1N1366A	CSR ETC IDC ♦INR INRJ MOTA MULB SAR SCN SES SOD SPE SSI	195-135	1N1371B	SAR	197-83	1N1359A	ESP GSE ♦INR INRI INRJ MOTA MULB SAR SCN SES SOD SPE SSI	193-18	1N1366B	TRW IDC IDC INRB INRJ MOTA MULB SAR SCN SES SOD SPE SSI	195-136	1N1371	CSR ETC IDC ♦INR INRJ MOTA MULB SAR SCN SES SOD SPE SSI	197-81	1N1375A	ESP GSE ♦INR INRI INRJ MOTA MULB SAR SCN SES SOD SPE SSI	198-136						
1N1359B	IDC IDC INRB INRJ MOTA MULB SAR SCN SES SOD SPE SSI	193-19	1N1383B	IDC IDC INRB INRJ MOTA MULB SAR SCN SES SOD SPE SSI	194-132	1N1366A	CSR ETC IDC ♦INR INRJ MOTA MULB SAR SCN SES SOD SPE SSI	195-135	1N1371A	ESP GSE ♦INR INRI INRJ MOTA MULB SAR SCN SES SOD SPE SSI	197-83	1N1359B	IDC IDC INRB INRJ MOTA MULB SAR SCN SES SOD SPE SSI	193-19	1N1366B	TRW IDC IDC INRB INRJ MOTA MULB SAR SCN SES SOD SPE SSI	195-136	1N1371	CSR ETC IDC ♦INR INRJ MOTA MULB SAR SCN SES SOD SPE SSI	197-81	1N1375A	ESP GSE ♦INR INRI INRJ MOTA MULB SAR SCN SES SOD SPE SSI	198-136						
1N1360	CSR ETC IDC ♦INR INRI INRJ MOTA MULB SAR SCN SES SOD SPE SSI	193-102	1N1384	CSR ETC IDC ♦INR INRJ MOTA MULB SAR SCN SES SOD SPE SSI	194-205	1N1366A	CSR ETC IDC ♦INR INRJ MOTA MULB SAR SCN SES SOD SPE SSI	195-135	1N1371B	SAR	197-84	1N1360	CSR ETC IDC ♦INR INRI INRJ MOTA MULB SAR SCN SES SOD SPE SSI	193-102	1N1366B	TRW IDC IDC INRB INRJ MOTA MULB SAR SCN SES SOD SPE SSI	195-136	1N1371	CSR ETC IDC ♦INR INRJ MOTA MULB SAR SCN SES SOD SPE SSI	197-81	1N1375A	ESP GSE ♦INR INRI INRJ MOTA MULB SAR SCN SES SOD SPE SSI	198-136						
1N1360A	ESP GSE ♦INR INRI INRJ MOTA MULB SAR SCN SES SOD SPE SSI	193-103	1N1384A	ESP GSE ♦INR INRJ MOTA MULB SAR SCN SES SOD SPE SSI	194-206	1N1366A	CSR ETC IDC ♦INR INRJ MOTA MULB SAR SCN SES SOD SPE SSI	195-135	1N1371A	ESP GSE ♦INR INRI INRJ MOTA MULB SAR SCN SES SOD SPE SSI	197-84	1N1360A	ESP GSE ♦INR INRI INRJ MOTA MULB SAR SCN SES SOD SPE SSI	193-103	1N1366B	TRW IDC IDC INRB INRJ MOTA MULB SAR SCN SES SOD SPE SSI	195-136	1N1371	CSR ETC IDC ♦INR INRJ MOTA MULB SAR SCN SES SOD SPE SSI	197-81	1N1375A	ESP GSE ♦INR INRI INRJ MOTA MULB SAR SCN SES SOD SPE SSI	198-136						